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[STRUCTURE APPLIED TO A PHOTOLITHOGRAPHIC PROCESS AND METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE]

Abstract

A structure applied to a photolithographic process is provided. The structure comprises at least a film layer, an optical isolation layer, an anti-reflection coating and a photoresist layer sequentially formed over a substrate. In the photolithographic process, the optical isolation layer stops light from penetrating down to the film layer. Since the optical isolation layer is set up underneath the photoresist layer, light emitted from a light source during photo-exposure is prevented from reflecting from the substrate surface after passing through the film layer. Thus, the critical dimensions of the photolithographic process are unaffected by any change in the thickness of the film layer.